

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP624, TLP624-2, TLP624-4

Programmable Controllers
AC/DC-Input Module
Telecommunication

The TOSHIBA TLP624, -2 and -4 consist of a gallium arsenide infrared emitting diode optically coupled to a photo-transistor.

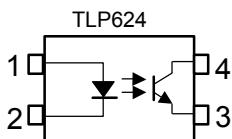
The TLP624-2 offers two isolated channels in an eight lead plastic DIP, while the TLP624-4 provides four isolated channels in a sixteen lead plastic DIP.

- Collector-emitter voltage: 55V min.
- Current transfer ratio

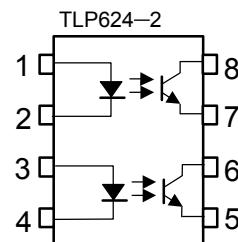
Classification	Current Transfer Ratio(min)			Marking of classification
	Ta = 25°C		Ta=-25~75°C	
	I _F =1mA V _{CE} =0.5V	I _F =0.5mA V _{CE} =1.5V	I _F =1mA V _{CE} =0.5V	
Rank BV	200%	100%	100%	BV
Standard	100%	50%	50%	BV,blank

- Isolation voltage: 5000V_{rms} min.
- UL recognized: UL1577, file No.E67349
- BSI approved: BS EN60065: 1994 Certificate No.7426
BS EN60950: 1992 Certificate No.7427
- Note: Application type name for certification test, please use standard product type name, i.e.
TLP624(BV): TLP624
TLP624-2(BV): TLP624-2

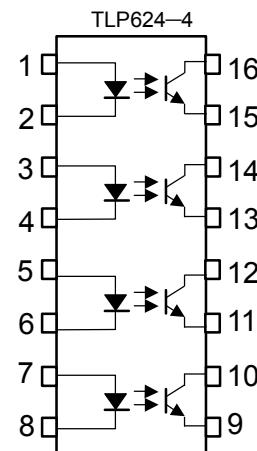
Pin Configurations (top view)



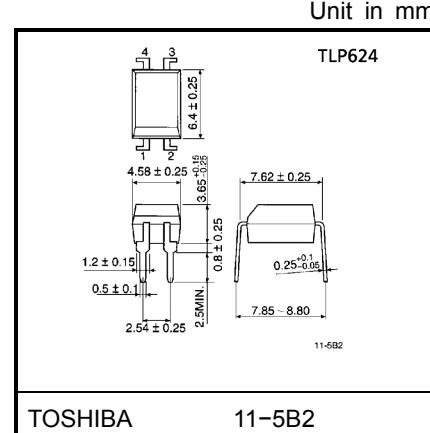
1. Anode
2. Cathode
3. Emitter
4. Collector



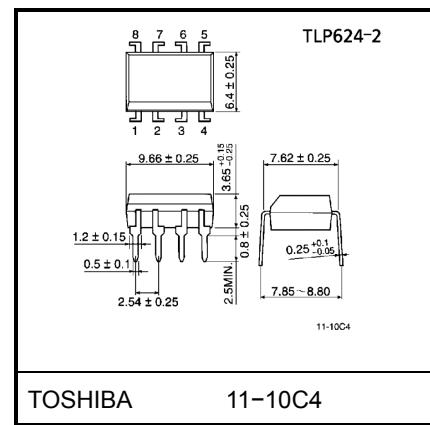
- 1,3 : Anode
2,4 : Cathode
5,7 : Emitter
6,8 : Collector



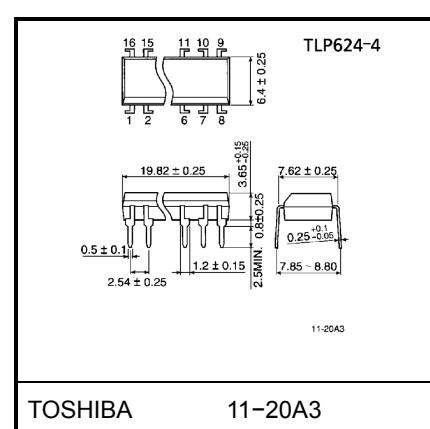
- 1,3,5,7: Anode
2,4,6,8: Cathode
9,11,13,15: Emitter
10,12,14,16: Collector



Weight: 0.26 g



Weight: 0.54 g



Weight: 1.1 g

Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Characteristic	Symbol	Rating		Unit
			TLP624	TLP624-2 TLP624-4	
LED	Forward current	I_F	60	50	mA
	Forward current derating	$\Delta I_F / ^\circ\text{C}$	-0.7($T_a \geq 39^\circ\text{C}$)	-0.5($T_a \geq 25^\circ\text{C}$)	mA / $^\circ\text{C}$
	Pulse forward current	I_{FP}	1(100 μs , pulse, 100pps)		A
	Power dissipation(1 Circuit)	P_D	100	70	mW
	Power dissipation derating ($T_a \geq 25^\circ\text{C}$, 1 Circuit)	$\Delta P_D / ^\circ\text{C}$	-1.0	-0.7	mW / $^\circ\text{C}$
	Reverse voltage	V_R	5		V
	Junction temperature	T_j	125		$^\circ\text{C}$
Detector	Collector-emitter voltage	V_{CEO}	55		V
	Emitter-collector voltage	V_{ECO}	7		V
	Collector current	I_C	50		mA
	Collector power dissipation(1 circuit)	P_C	150	100	mW
	Collector power dissipation derating ($T_a \geq 25^\circ\text{C}$, 1 Circuit)	$\Delta P_C / ^\circ\text{C}$	-1.5	-1.0	mW / $^\circ\text{C}$
	Junction temperature	T_j	125		$^\circ\text{C}$
	Storage temperature range	T_{stg}	-55~125		$^\circ\text{C}$
Operating temperature range		T_{opr}	-55~100		$^\circ\text{C}$
Lead soldering temperature		T_{sol}	260(10s)		$^\circ\text{C}$
Total package power dissipation(1 Circuit)		P_T	250	150	mW
Total package power dissipation derating ($T_a \geq 25^\circ\text{C}$, 1 Circuit)		$\Delta P_T / ^\circ\text{C}$	-2.5	-1.5	mW / $^\circ\text{C}$
Isolation voltage (Note 1)		BV_S	5000(AC, 1min., RH≤60%)		Vrms

(Note 1) Device considered a two terminal device: LED side pins shorted together, and detector side pins shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	—	5	24	V
Forward current	I_F	—	1.6	20	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	-25	—	75	$^\circ\text{C}$

Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V _F	I _F = 10mA	1.0	1.15	1.3	V
	Reverse current	I _R	V _R = 5V	—	—	10	µA
	Capacitance	C _T	V = 0, f = 1MHz	—	30	—	pF
Detector	Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 0.5mA	55	—	—	V
	Emitter-collector breakdown voltage	V _{(BR)ECO}	I _E = 0.1mA	7	—	—	V
	Collector dark current	I _{CEO}	V _{CE} = 24V	—	10	100	nA
			V _{CE} = 24V, Ta = 85°C	—	2	50	µA
	Capacitance collector to emitter	C _{CE}	V=0, f=1MHz	—	12	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I _C / I _F	I _F = 1mA, V _{CE} = 0.5V Rank BV	100	—	1200	%
			200	—	1200	
Low input CTR	I _C / I _F (low)	I _F = 0.5mA, V _{CE} = 1.5V Rank BV	50	—	—	%
			100	—	—	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = 0.5mA, I _F = 1mA	—	—	0.4	V
		I _C = 1mA, I _F = 1mA Rank BV	—	0.2	—	
			—	—	0.4	

Coupled Electrical Characteristics (Ta = -25°C~75°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I _C / I _F	I _F = 1mA, V _{CE} = 0.5V Rank BV	50	—	—	%
			100	—	—	
Low input CTR	I _C / I _F (low)	I _F = 0.5mA, V _{CE} = 1.5V Rank BV	—	50	—	%
			—	100	—	

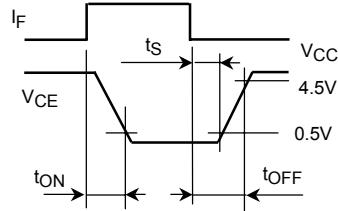
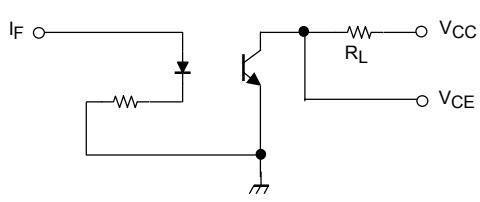
Isolation Characteristics (Ta = 25°C)

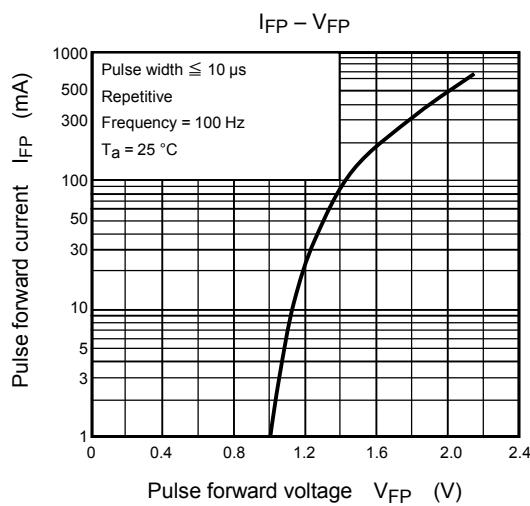
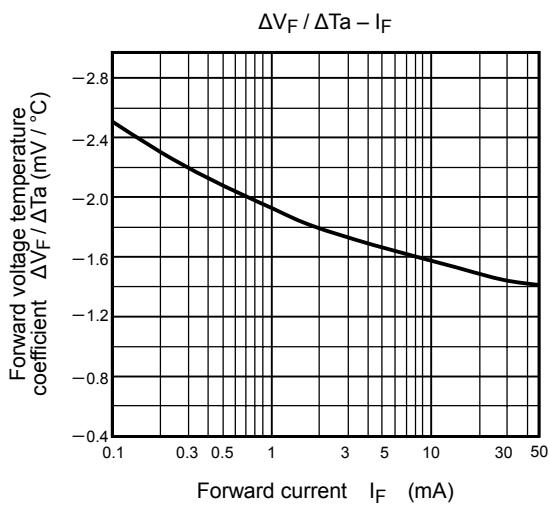
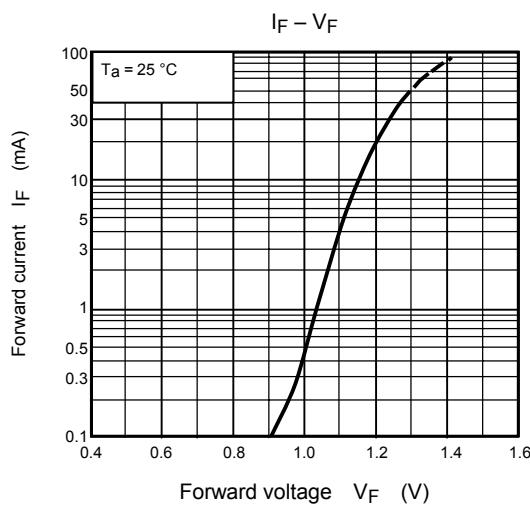
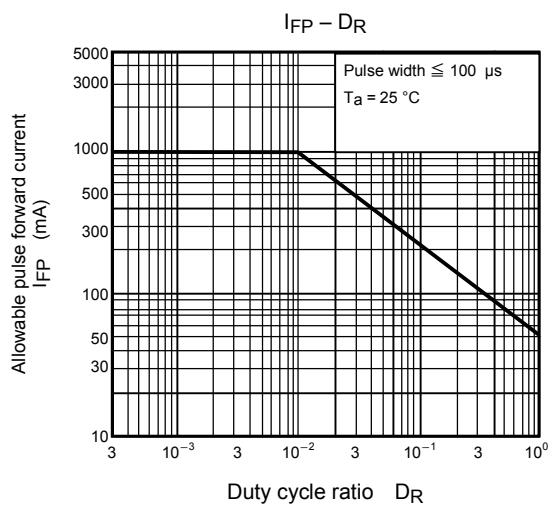
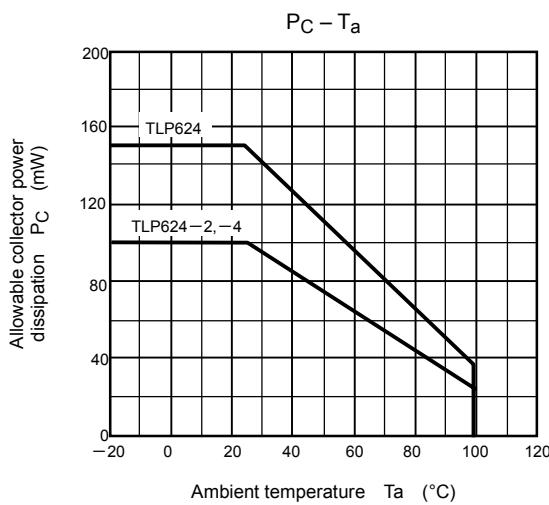
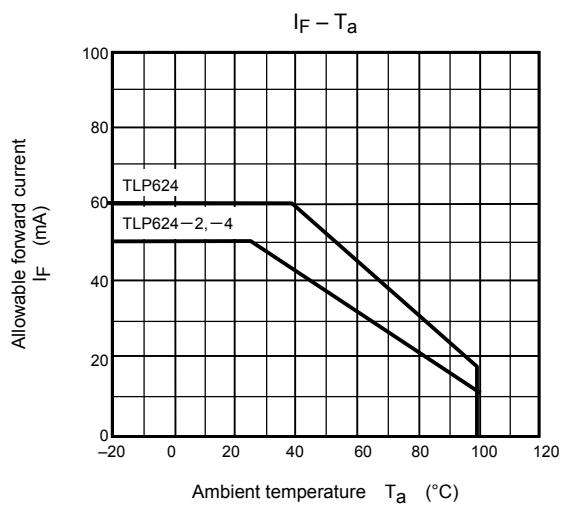
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance input to output	C _S	V _S = 0, f = 1MHz	—	0.8	—	pF
Isolation resistance	R _S	V _S = 500V	5×10 ¹⁰	10 ¹⁴	—	Ω
Isolation voltage	BV _S	AC, 1minute	5000	—	—	V _{rms}
		AC, 1second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V _{dc}

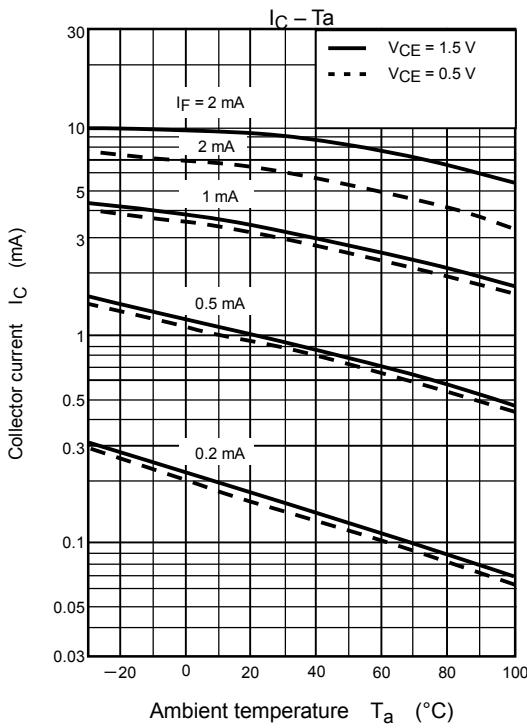
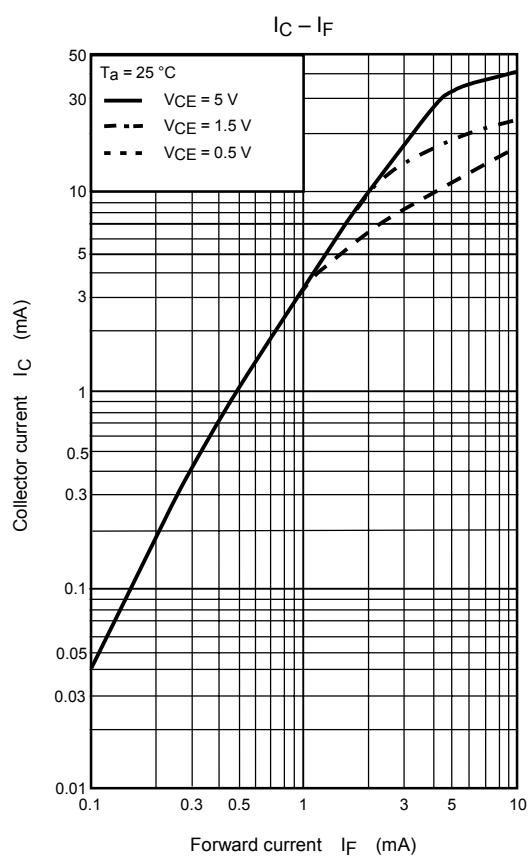
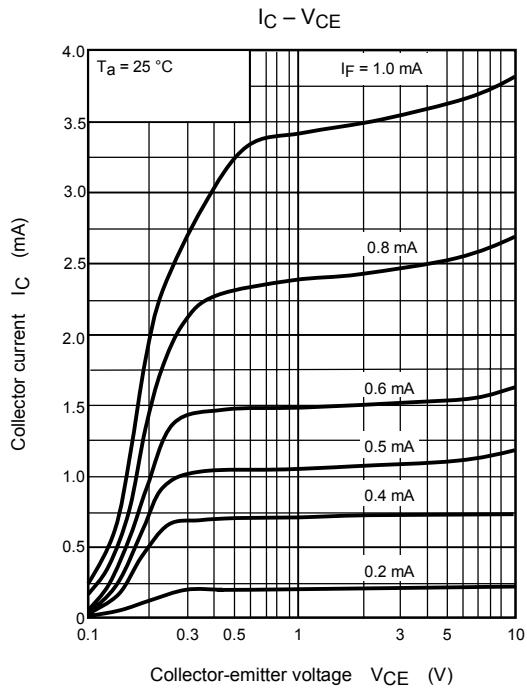
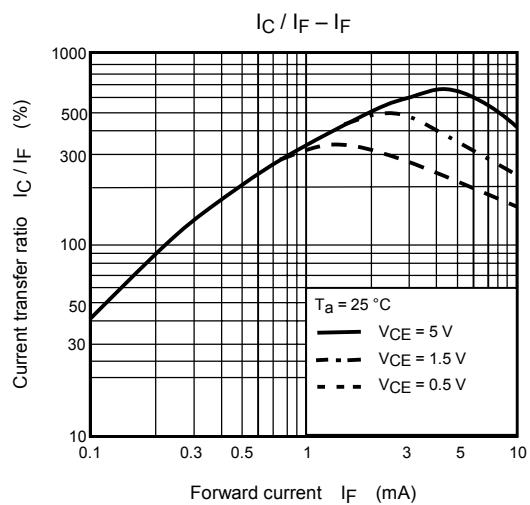
Switching Characteristics (Ta = 25°C)

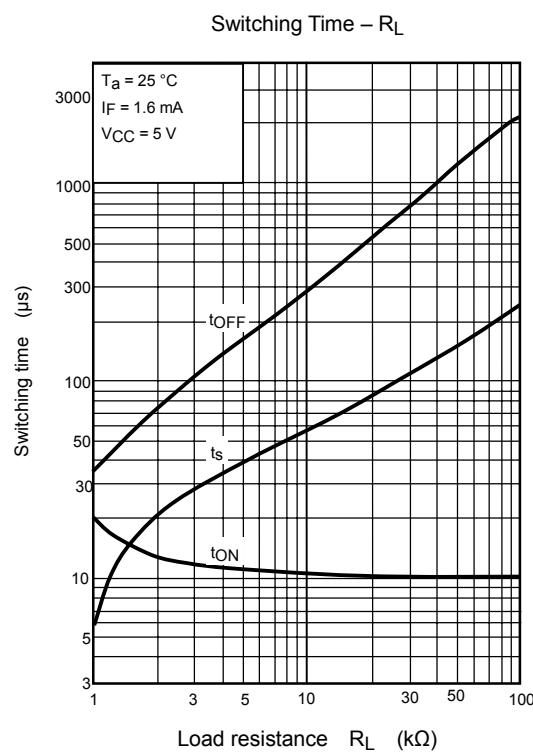
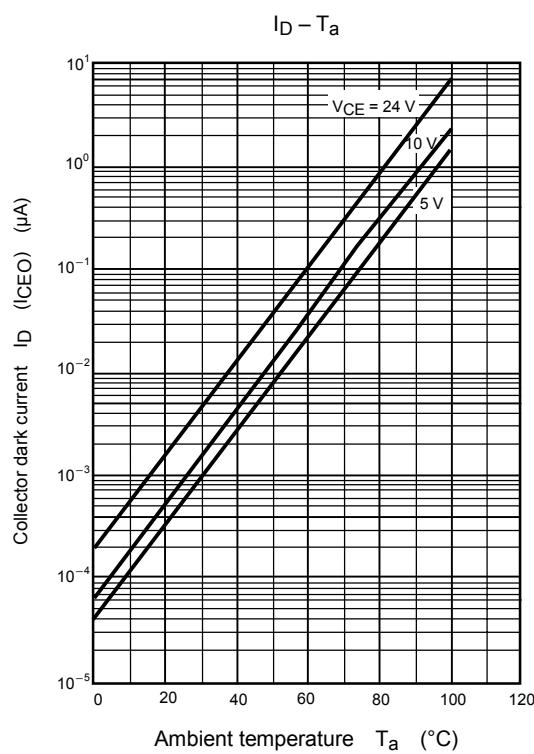
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t _r	V _{CC} = 10V, I _C = 2mA R _L = 100Ω	—	8	—	μs
Fall time	t _f		—	8	—	
Turn-on time	t _{on}		—	10	—	
Turn-off time	t _{off}		—	8	—	
Turn-on time	t _{ON}	R _L = 4.7 kΩ (Fig.1) V _{CC} = 5 V, I _F = 1.6mA	—	10	—	μs
Storage time	t _S		—	50	—	
Turn-off time	t _{OFF}		—	300	—	

Fig. 1 Switching time test circuit









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